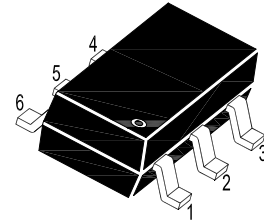
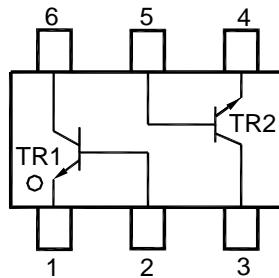


# BC846DW...BC850DW

## NPN Silicon Epitaxial Planar Transistor

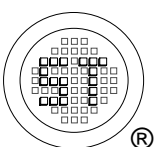
for general purpose and switching applications



1. Emitter 2. Base 3. Collector  
4. Emitter 5. Base 6. Collector  
SOT-363 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Collector Base Voltage	$V_{CBO}$	BC846DW	80	V
		BC847DW	50	
		BC848DW	30	
		BC849DW	30	
		BC850DW	50	
Collector Emitter Voltage	$V_{CEO}$	BC846DW	65	V
		BC847DW	45	
		BC848DW	30	
		BC849DW	30	
		BC850DW	45	
Emitter Base Voltage	$V_{EBO}$	BC846DW	6	V
		BC847DW	6	
		BC848DW	5	
		BC849DW	5	
		BC850DW	5	
Collector Current	$I_C$	100	mA	
Peak Collector Current	$I_{CM}$	200	mA	
Total Power Dissipation	$P_{tot}$	250	mW	
Junction Temperature	$T_j$	150	$^\circ\text{C}$	
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$	



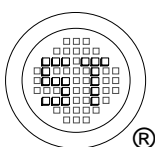
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# BC846DW...BC850DW

## Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$ , $I_C = 2\text{ mA}$	BC846ADW~BC850ADW	$h_{FE}$	110	220	-
	BC846BDW~BC850BDW	$h_{FE}$	200	450	-
	BC846CDW~BC850CDW	$h_{FE}$	420	800	-
Collector Base Voltage at $I_C = 10\text{ }\mu\text{A}$	BC846DW	$V_{CBO}$	80	-	V
	BC847DW		50	-	
	BC848DW		30	-	
	BC849DW		30	-	
	BC850DW		50	-	
Collector Emitter Voltage at $I_C = 10\text{ mA}$	BC846DW	$V_{CEO}$	65	-	V
	BC847DW		45	-	
	BC848DW		30	-	
	BC849DW		30	-	
	BC850DW		45	-	
Emitter Base Voltage at $I_E = 1\text{ }\mu\text{A}$	BC846DW	$V_{EBO}$	6	-	V
	BC847DW		6	-	
	BC848DW		5	-	
	BC849DW		5	-	
	BC850DW		5	-	
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	$I_{CBO}$	-	15	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	$I_{EBO}$	-	100	nA	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.25	V	
		-	0.6		
Base Emitter Voltage at $V_{CE} = 5\text{ V}$ , $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$	$V_{BE}$	0.58	0.7	V	
		-	0.77		
Transition Frequency at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	100	-	MHz	
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	$C_{ob}$	-	4.5	pF	



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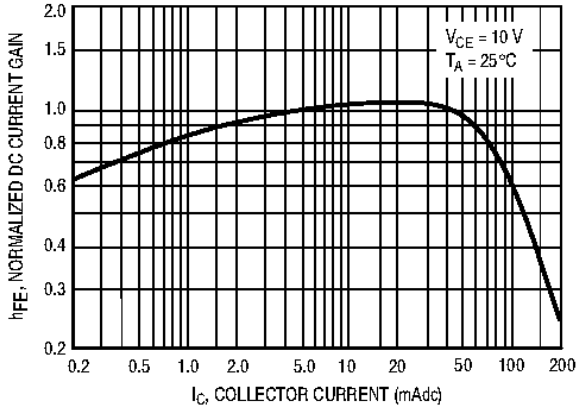


Figure 1. Normalized DC Current Gain

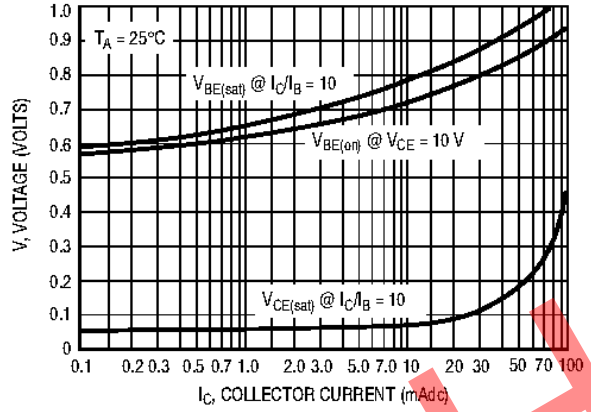


Figure 2. "Saturation" and "On" Voltages

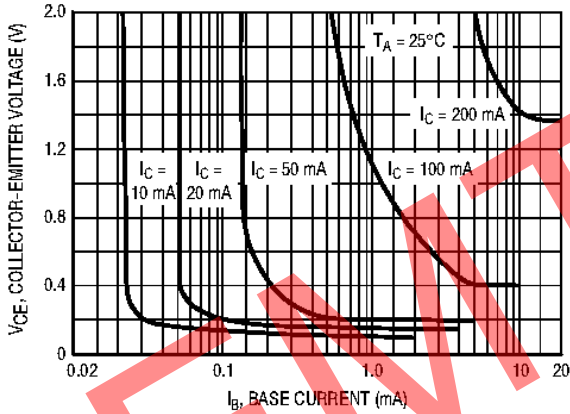


Figure 3. Collector Saturation Region

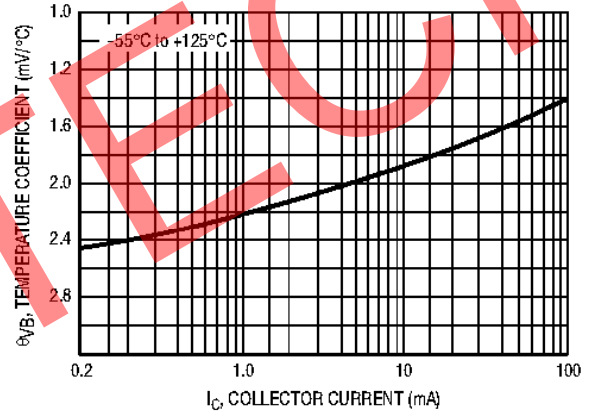


Figure 4. Base-Emitter Temperature Coefficient

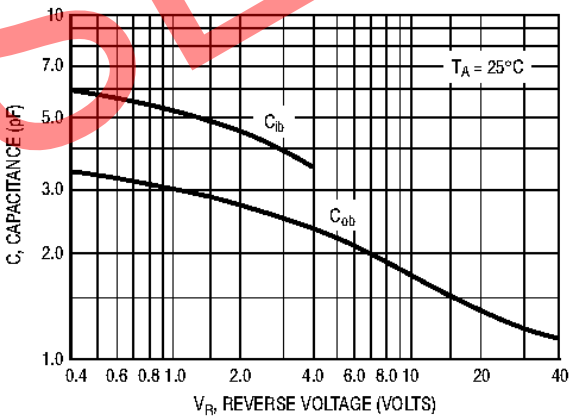


Figure 5. Capacitances

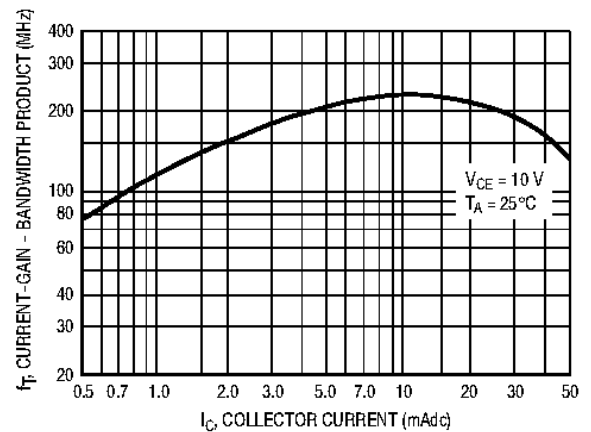
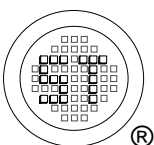


Figure 6. Current-Gain - Bandwidth Product



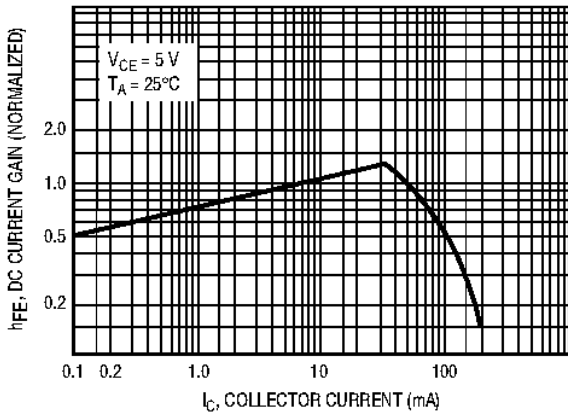


Figure 7. DC Current Gain

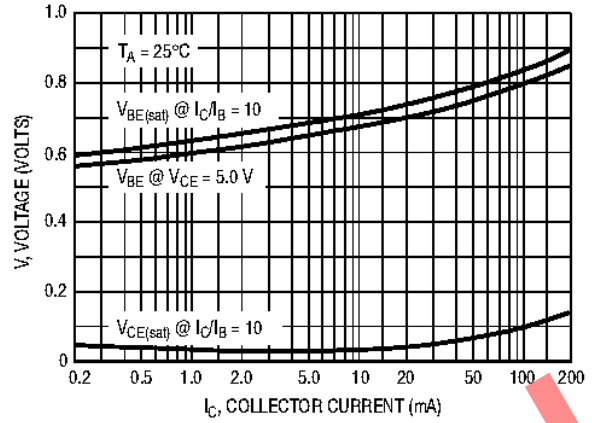


Figure 8. "On" Voltage

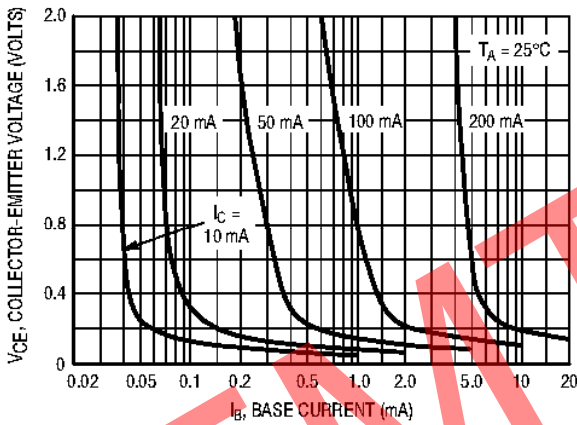


Figure 9. Collector Saturation Region

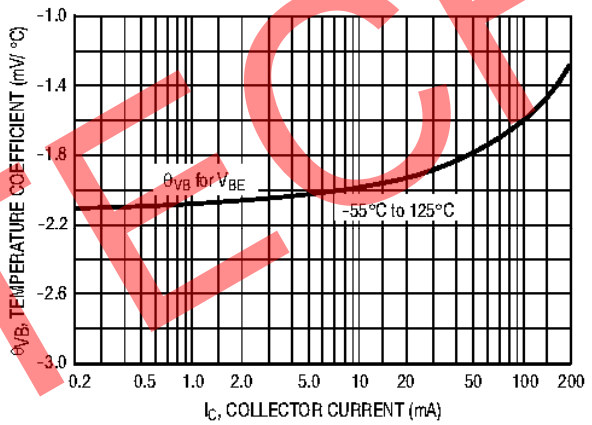


Figure 10. Base-Emitter Temperature Coefficient

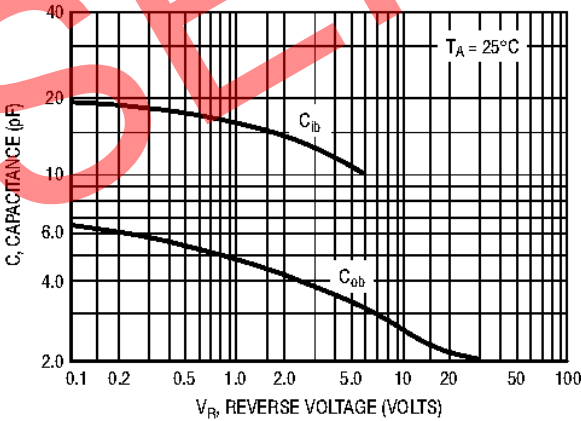


Figure 11. Capacitance

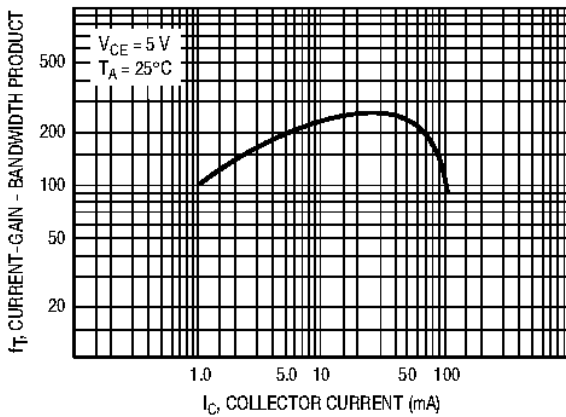


Figure 12. Current-Gain - Bandwidth Product

